



N 沟道增强型场效应晶体管

N-CHANNEL MOSFET

FHP80N06B/FHS80N06B/FHD80N06B

主要参数 MAIN CHARACTERISTICS

ID	80A
VDSS	60 V
Rdson-typ (@Vgs=10V)	6.2 mΩ
Qg-typ	72nC

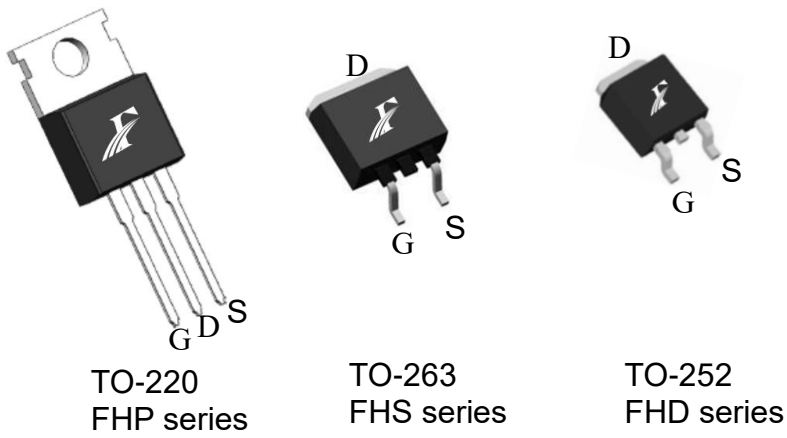
用途 APPLICATIONS

电机驱动	Motor drive
高频开关电源	Hard switched and High frequency circuits
不间断电源	UPS

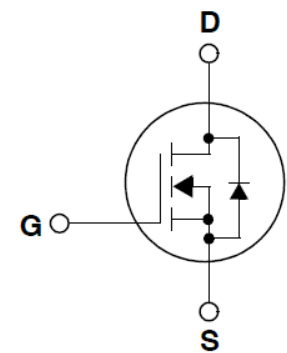
产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 240pF)	Low Crss (typical240pF)
开关速度快	Fast switching
100%经过 Rg 测试	100% Rg tested
100%经过雪崩测试	100% avalanche tested
100%经过热阻测试	100% DVDS tested
Trench 工艺	Trench process
RoHS 产品	RoHS product

封装形式 Package



等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项目 Parameter	符号 Symbol	数值 Value		单位 Unit
		FHP/S80N06B	FHD80N06B	
最高漏极-源极直流电压 Drain-Source Voltage	V _{DS}	60		V
连续漏极电流* Drain Current -continuous *	I _D (T _C =25°C)	80		A
	I _D (T _C =100°C)	60		A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	I _{DM}	320		A
最高栅源电压 Gate-Source Voltage	V _{GS}	±20		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E _{AS}	98		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I _{AR}	14		A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	E _{AR}	11		mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0		V/ns
耗散功率 Power Dissipation	P _D (T _C =25°C)	107	75	W
	-Derate above 25°C	0.85	0.6	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150		°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300		°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏-源击穿电压 Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	60	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, referenced to 25°C	-	0.06	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V, T _C =25°C	-	-	1	μA
		V _{DS} =48V, T _C =125°C	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I _{GSS} (F/R)	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	2	3	4	V
静态导通电阻 Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V , I _D =20A	-	6.2	7.5	mΩ
正向跨导 Forward Transconductance	g _{fs}	V _{DS} = 10V, I _D =20A (note 4)	-	25	-	S
动态特性 Dynamic Characteristics						
栅电阻 Gate Resistance	R _g	f=1.0MHz, V _{DS} OPEN	-	1.3	-	Ω
输入电容 Input capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1.0MHz	-	3000	-	pF
输出电容 Output capacitance	C _{oss}		-	270	-	
反向传输电容 Reverse transfer capacitance	C _{rss}		-	240	-	
开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	t _{d(on)}	V _{DD} =30V, I _D =30A, R _G =3Ω V _{GS} =10V (note 4, 5)	-	8.5	-	ns
上升时间 Turn-On rise time	t _r		-	7	-	ns
延迟时间 Turn-Off delay time	t _{d(off)}		-	40	-	ns
下降时间 Turn-Off Fall time	t _f		-	15	-	ns
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =48V , I _D =40A , V _{GS} =10V (note 4, 5)	-	72	-	nC
栅-源电荷 Gate-Source charge	Q _{gs}		-	22	-	nC
栅-漏电荷 Gate-Drain charge	Q _{gd}		-	50	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		I _S	-	-	80	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}	-	-	320	A
正向压降 Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =40A	-	-	1.2	V
反向恢复时间 Reverse recovery time	t _{rr}	V _{GS} =0V, I _S =40A, dI _F /dt=100A/μs (note 4)	-	30	-	ns
反向恢复电荷 Reverse recovery charge	Q _{rr}		-	85	-	nC

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	FHP/S80N06B	FHD80N06B	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.17	1.67	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	62.5	62.5	°C/W

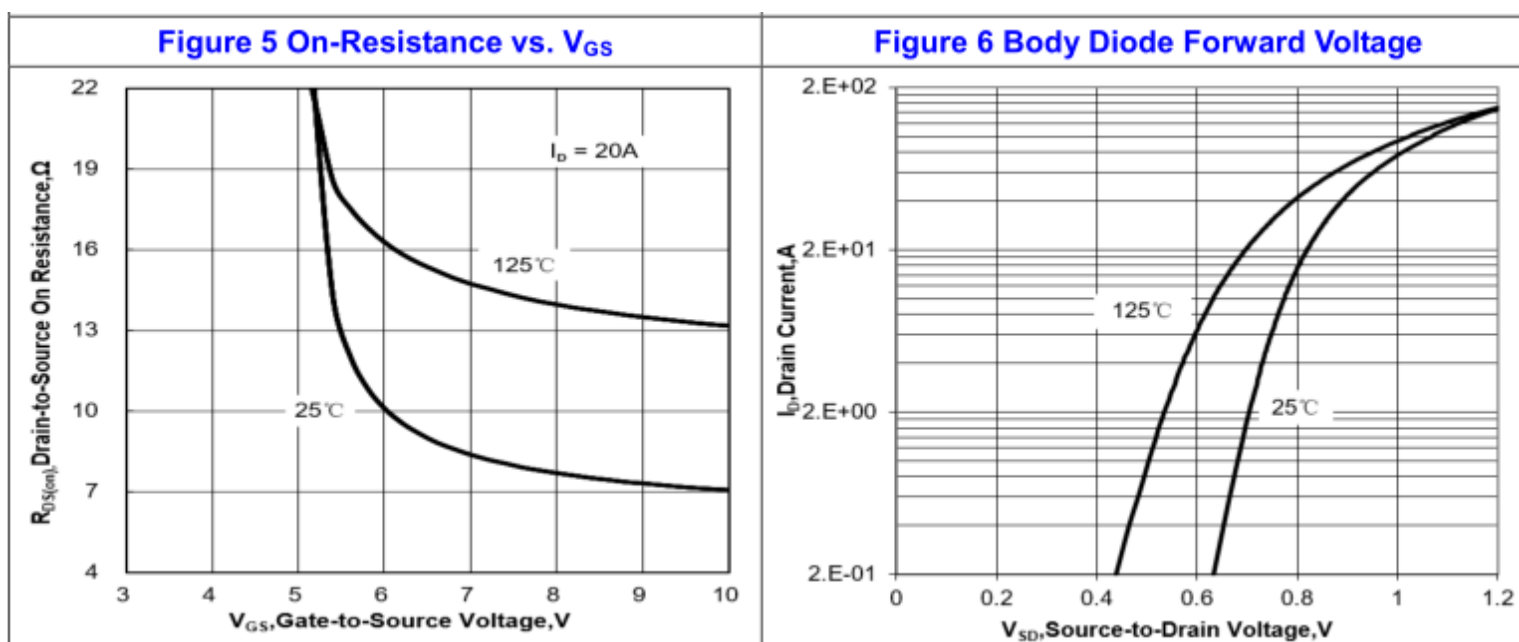
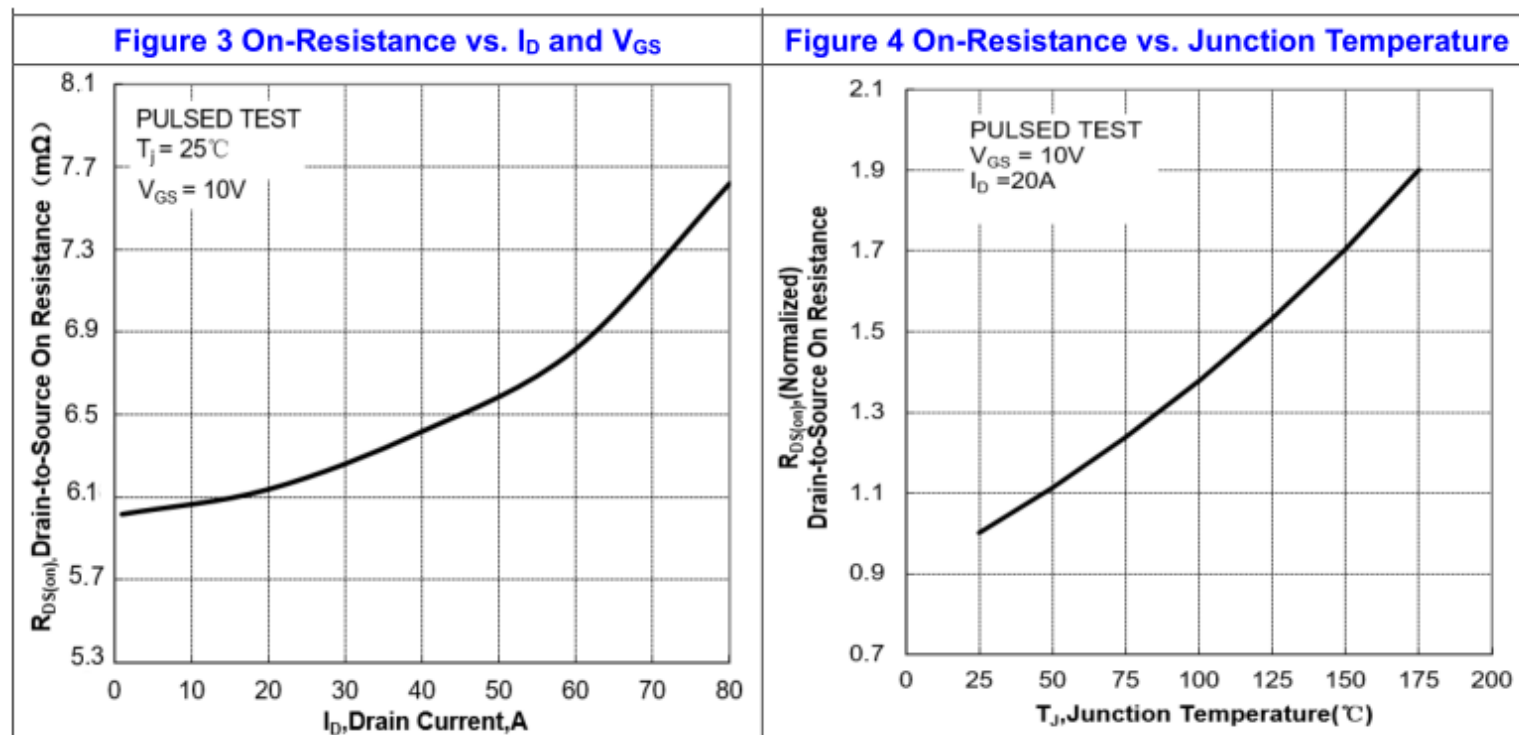
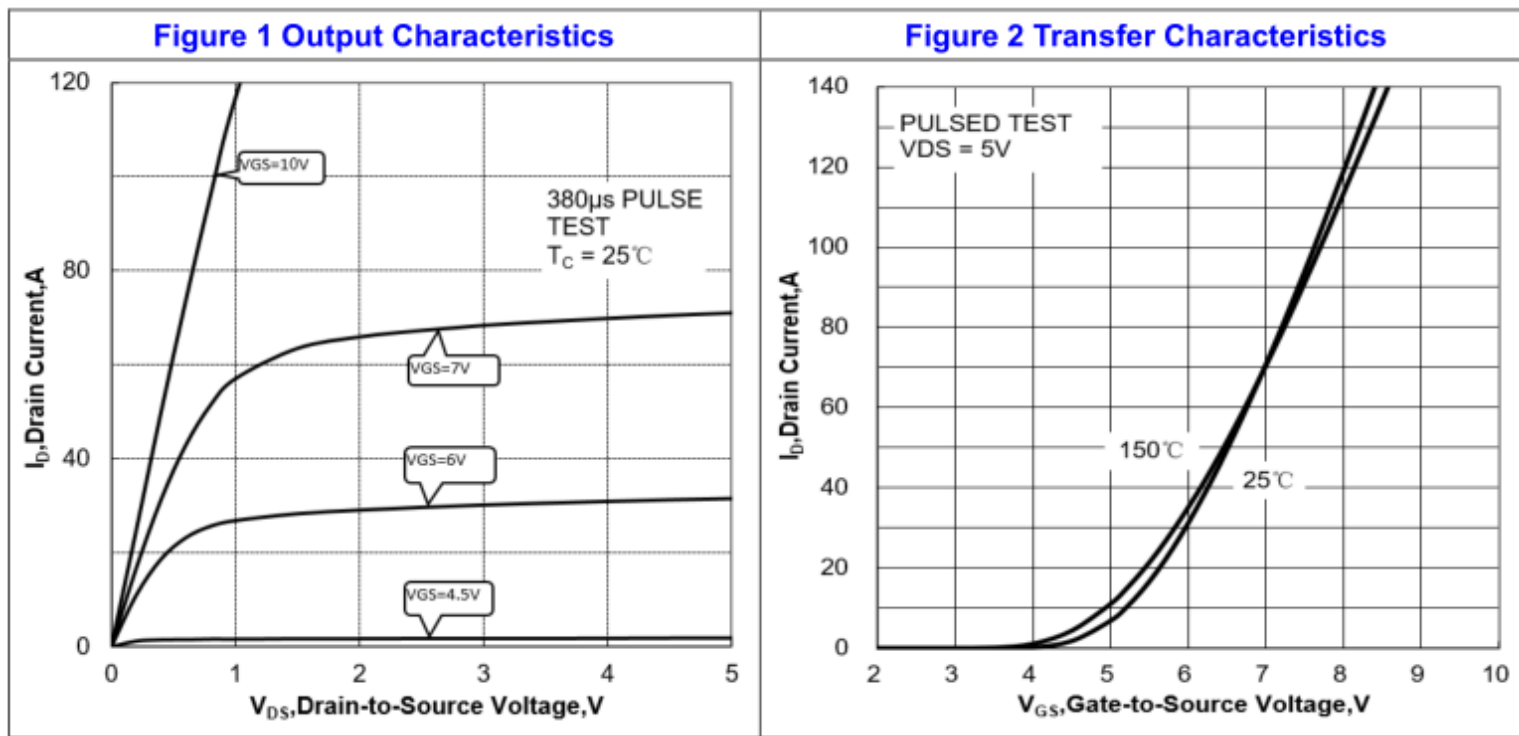
注释:

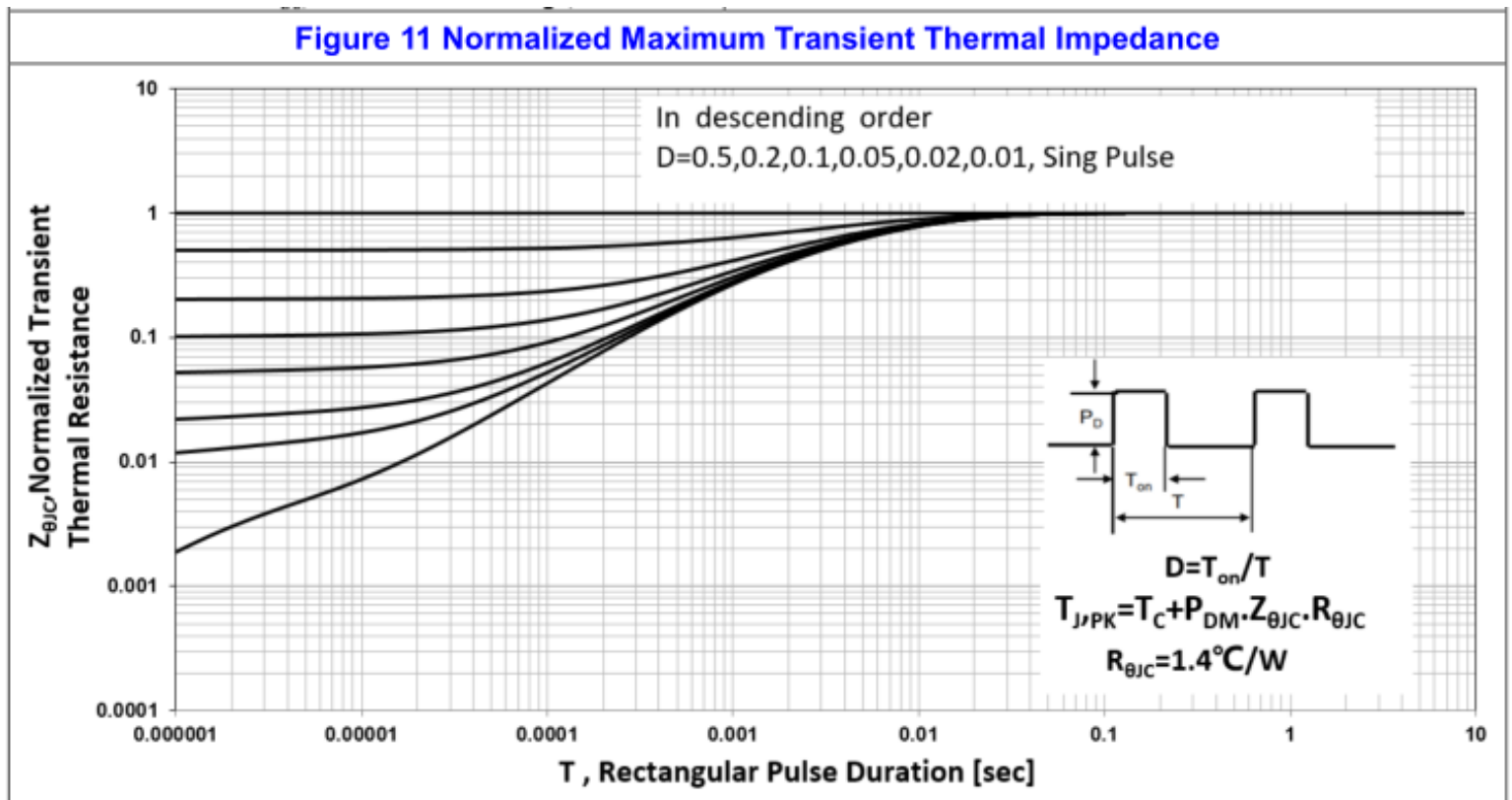
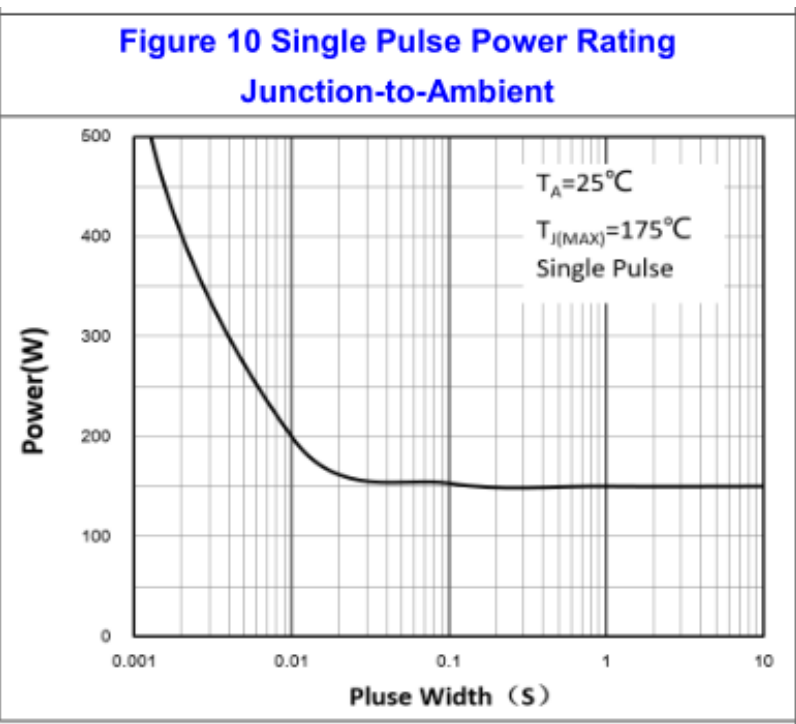
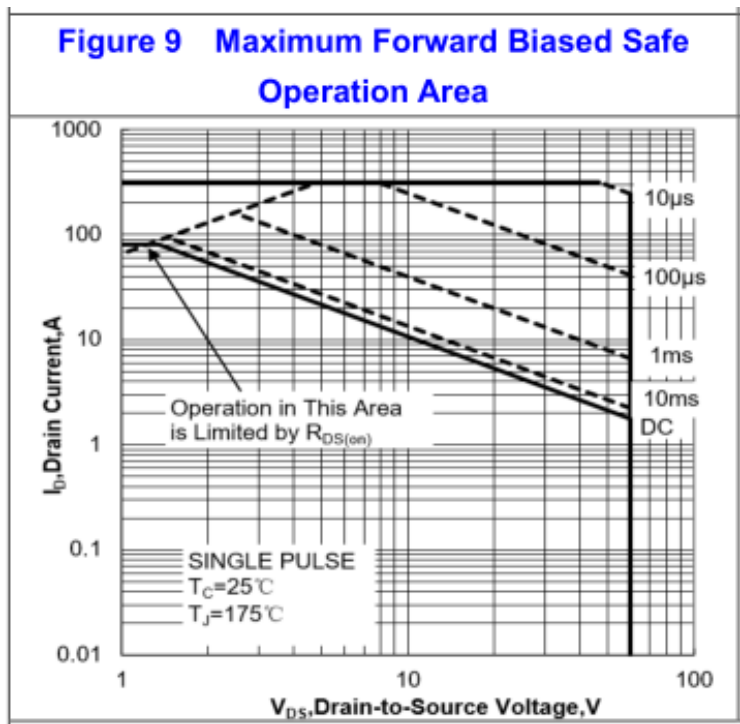
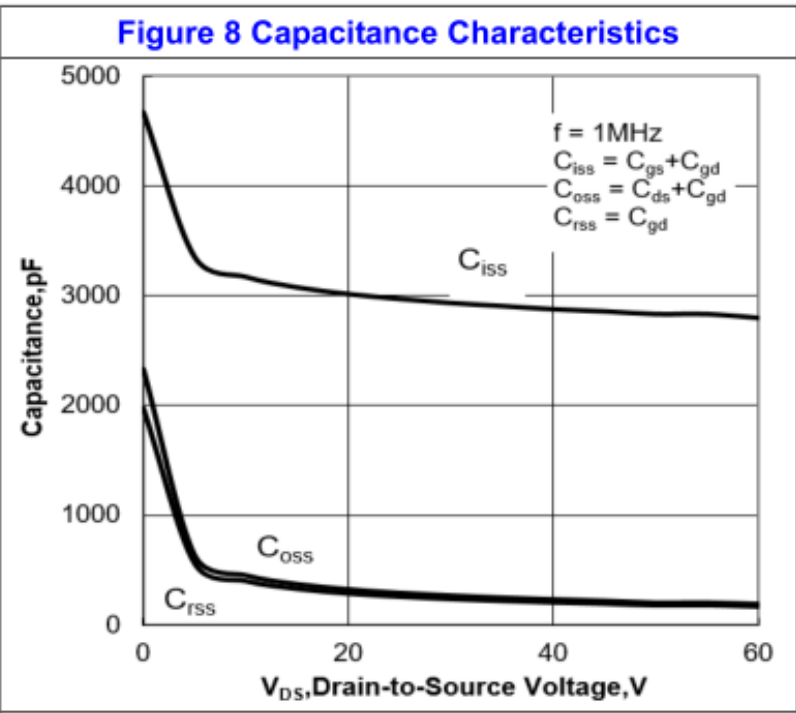
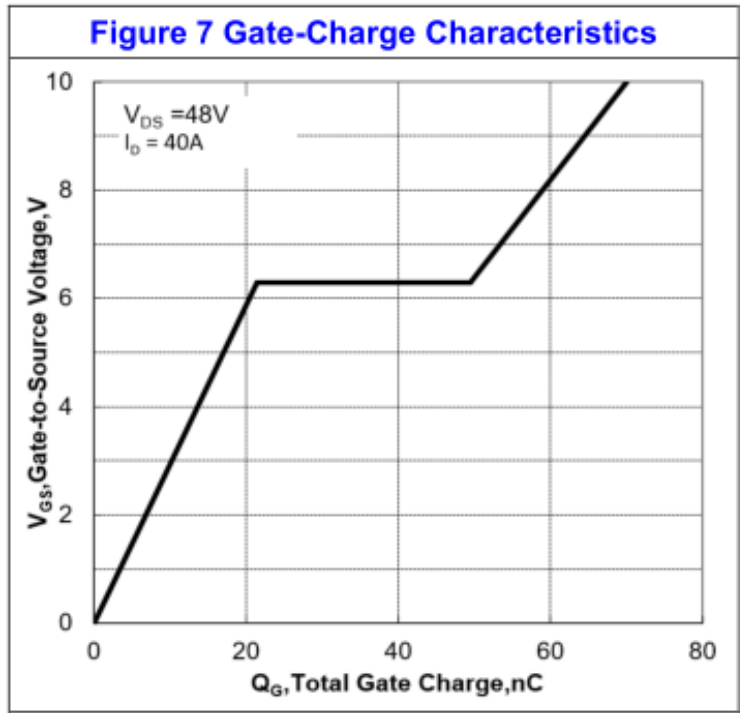
- 1: 脉冲宽度由最高结温限制
- 2: L=1mH, I_{AS}=14A, V_{DD}=48V, R_G=25 Ω, 起始结温 T_J=25°C
- 3: I_{SD} ≤80A, di/dt ≤300A/μs, V_{DD} ≤BV_{DSS}, 起始结温 T_J=25°C
- 4: 脉冲测试: 脉冲宽度 ≤300μs, 占空比 ≤2%
- 5: 基本与工作温度无关

Notes:

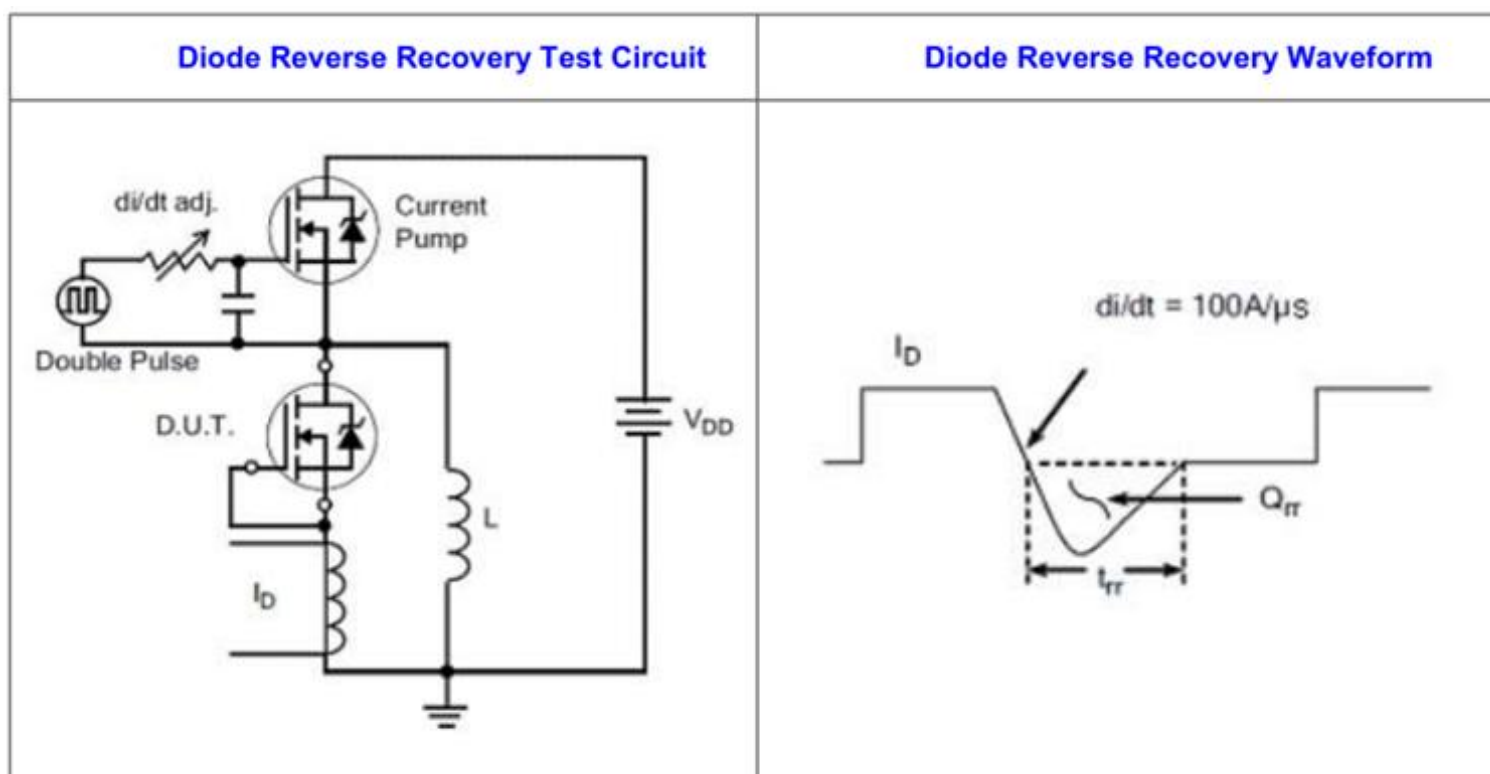
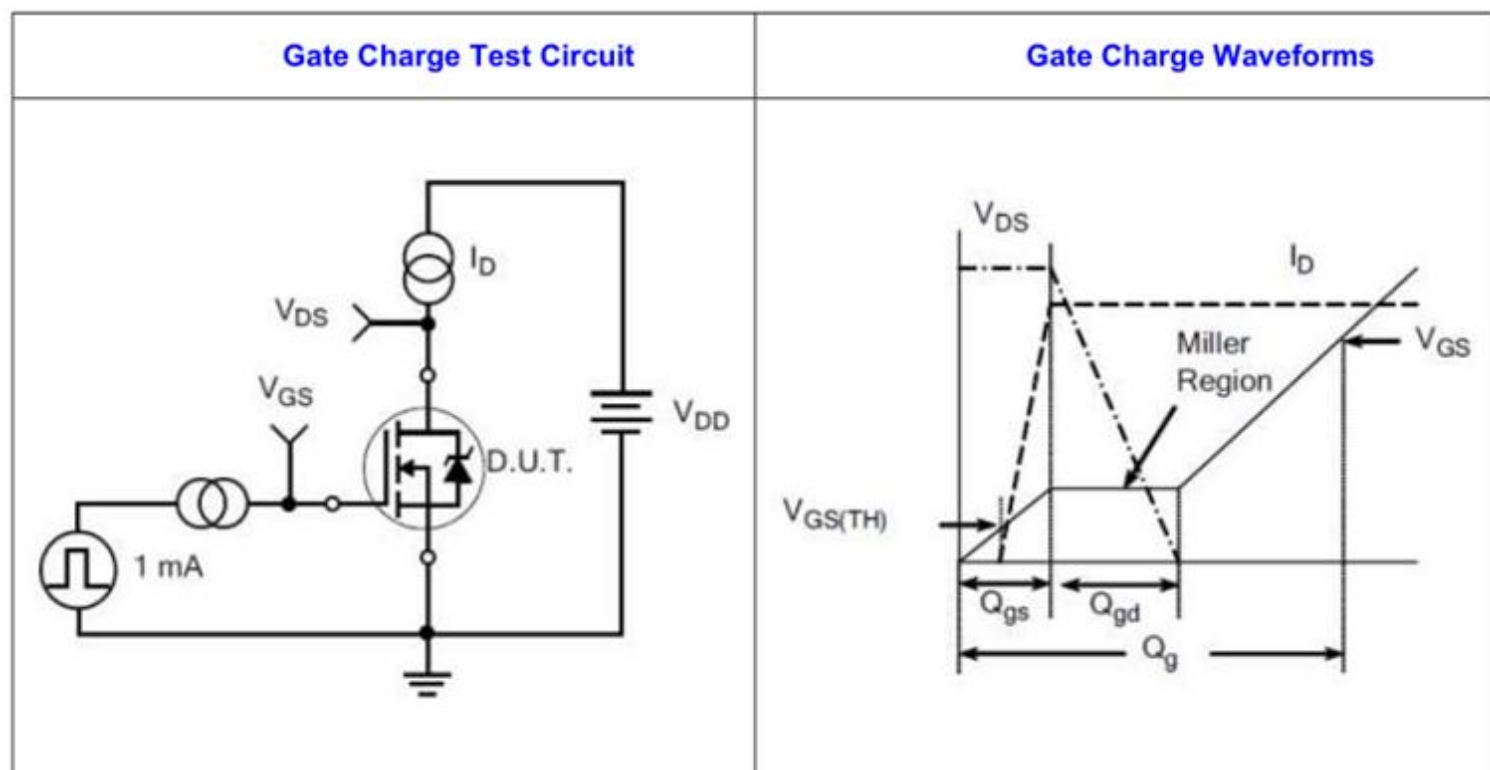
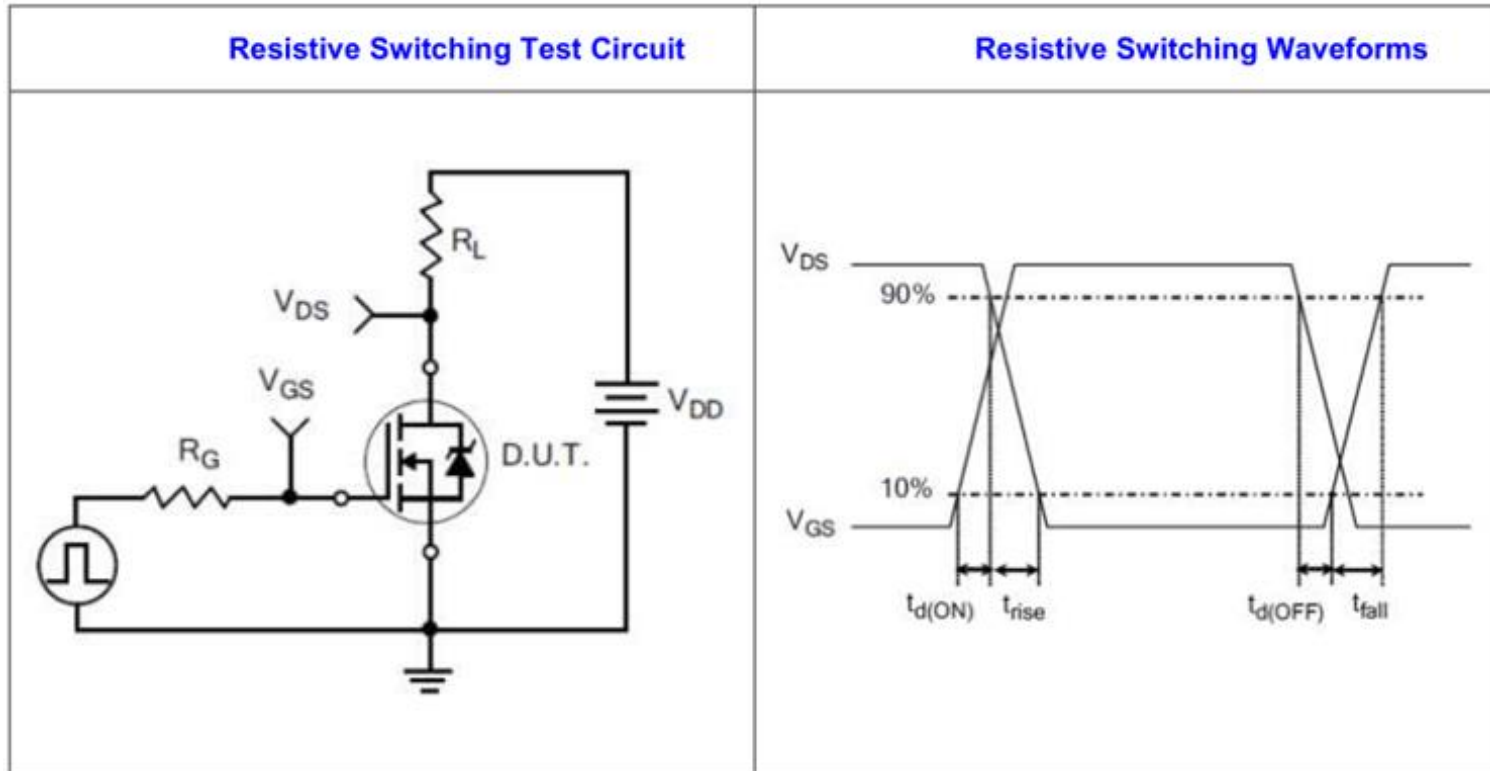
- 1: Pulse width limited by maximum junction temperature
- 2: L=1mH, I_{AS}=14A, V_{DD}=48V, R_G=25 Ω, Starting T_J=25°C
- 3: I_{SD} ≤80A, di/dt ≤300A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C
- 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%
- 5: Essentially independent of operating temperature

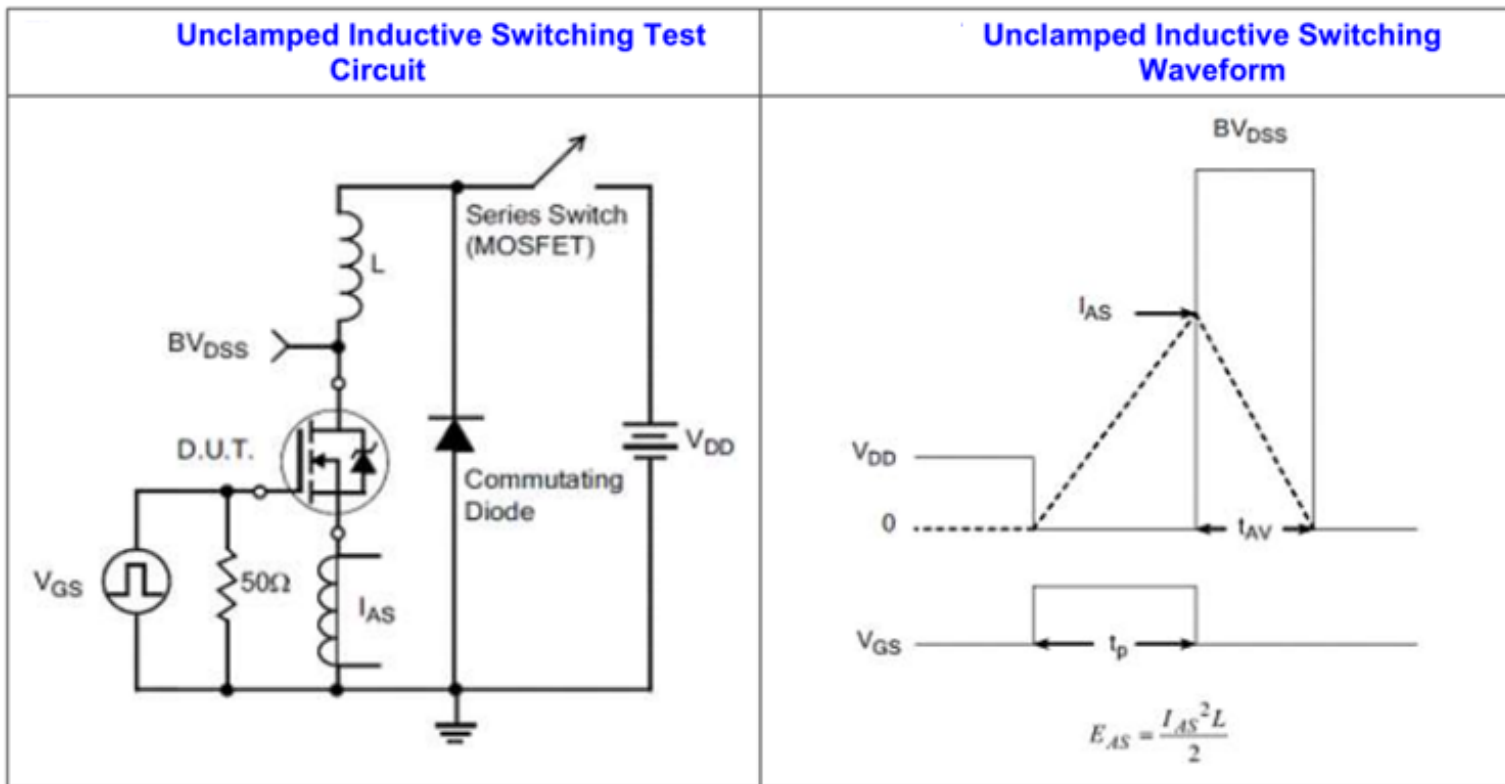
Typical Performance Characteristics



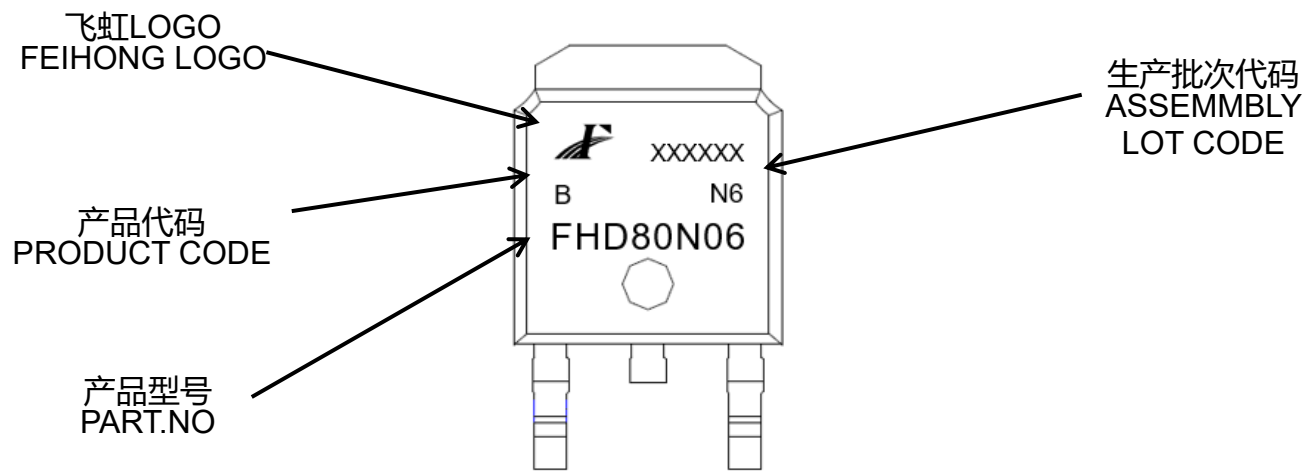
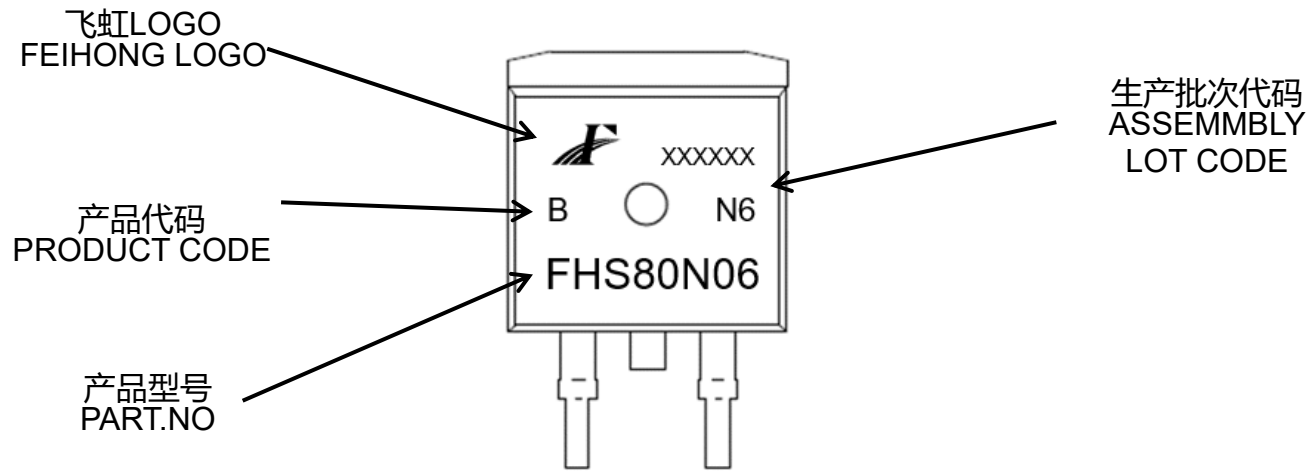
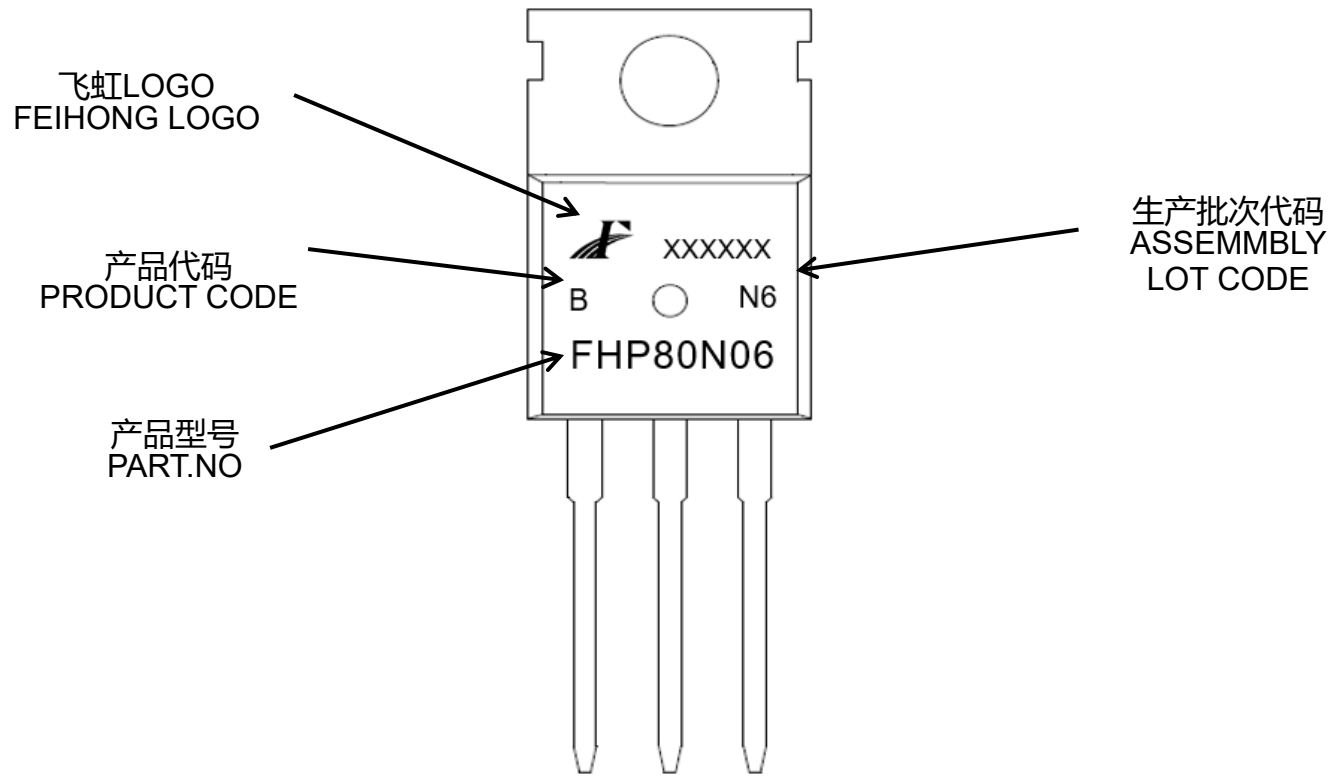


Test Circuit & Waveform





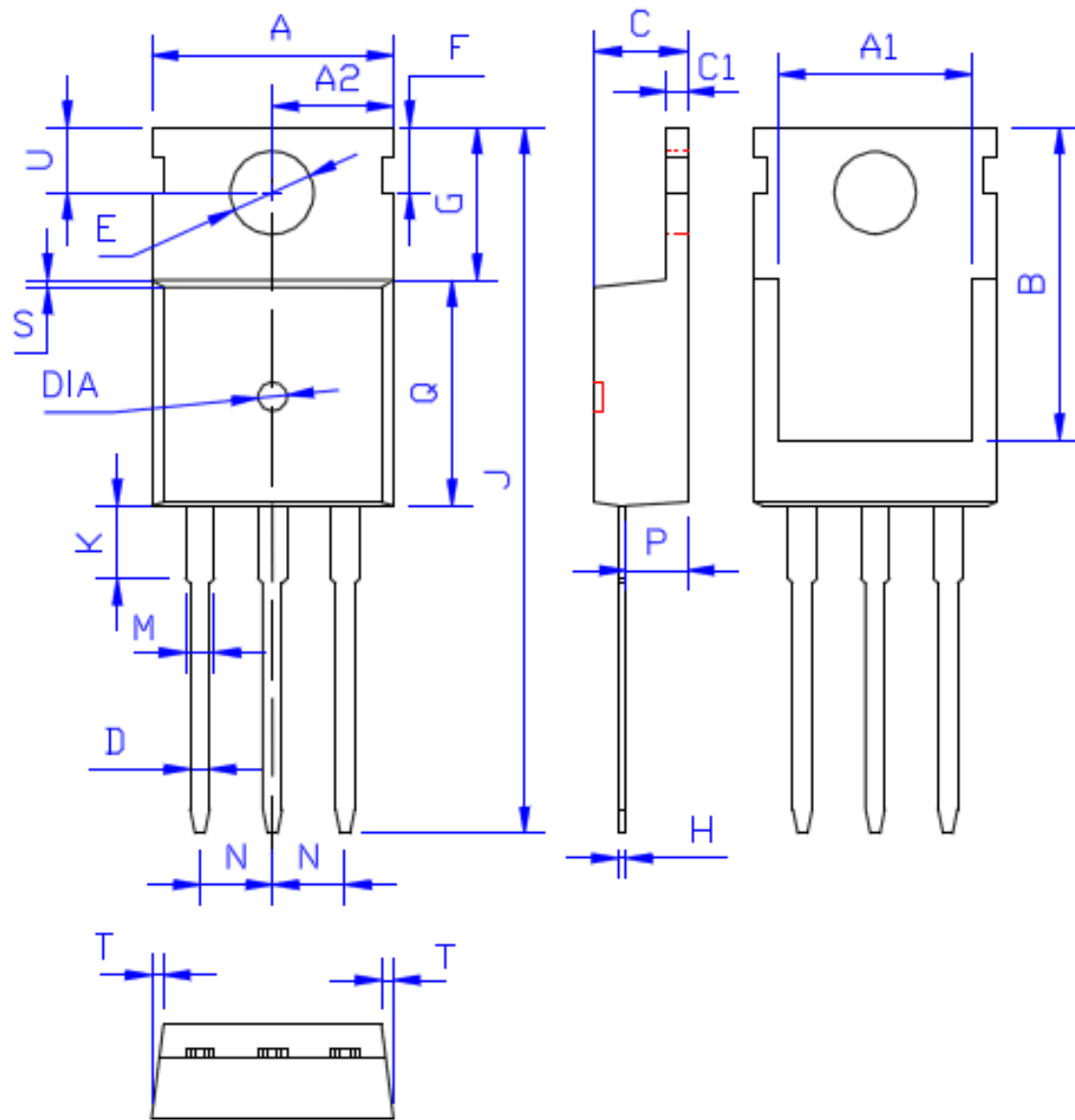
印记 Marking:



外形尺寸:

Package Dimension:

TO-220



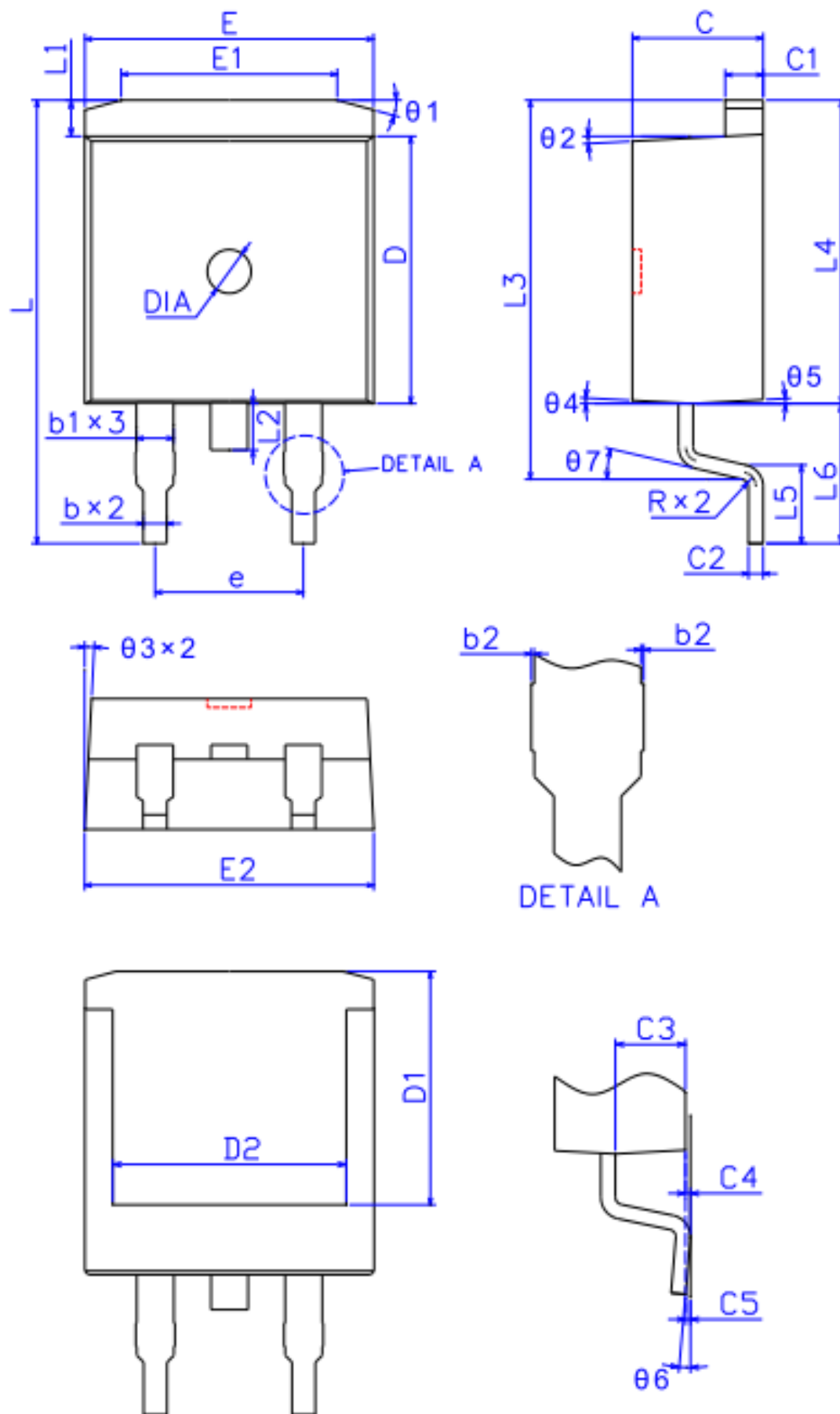
DIM	MILLIMETERS
A	10.00 ± 0.30
A1	8.00 ± 0.30
A2	5.00 ± 0.30
B	13.20 ± 0.40
C	4.50 ± 0.20
C1	1.30 ± 0.20
D	0.80 ± 0.20
E	3.60 ± 0.20
F	3.00 ± 0.30
G	6.60 ± 0.40
H	0.50 ± 0.20
J	28.88 ± 0.50
K	3.00 ± 0.30
M	1.30 ± 0.30
N	Typical 2.54
P	2.40 ± 0.40
Q	9.20 ± 0.40
S	0.25 ± 0.15
T	0.25 ± 0.15
U	2.80 ± 0.30
DIA	宽 1.50 ± 0.10 深 0.50 MAX

(Unit: mm)

外形尺寸:

Package Dimension:

TO-263

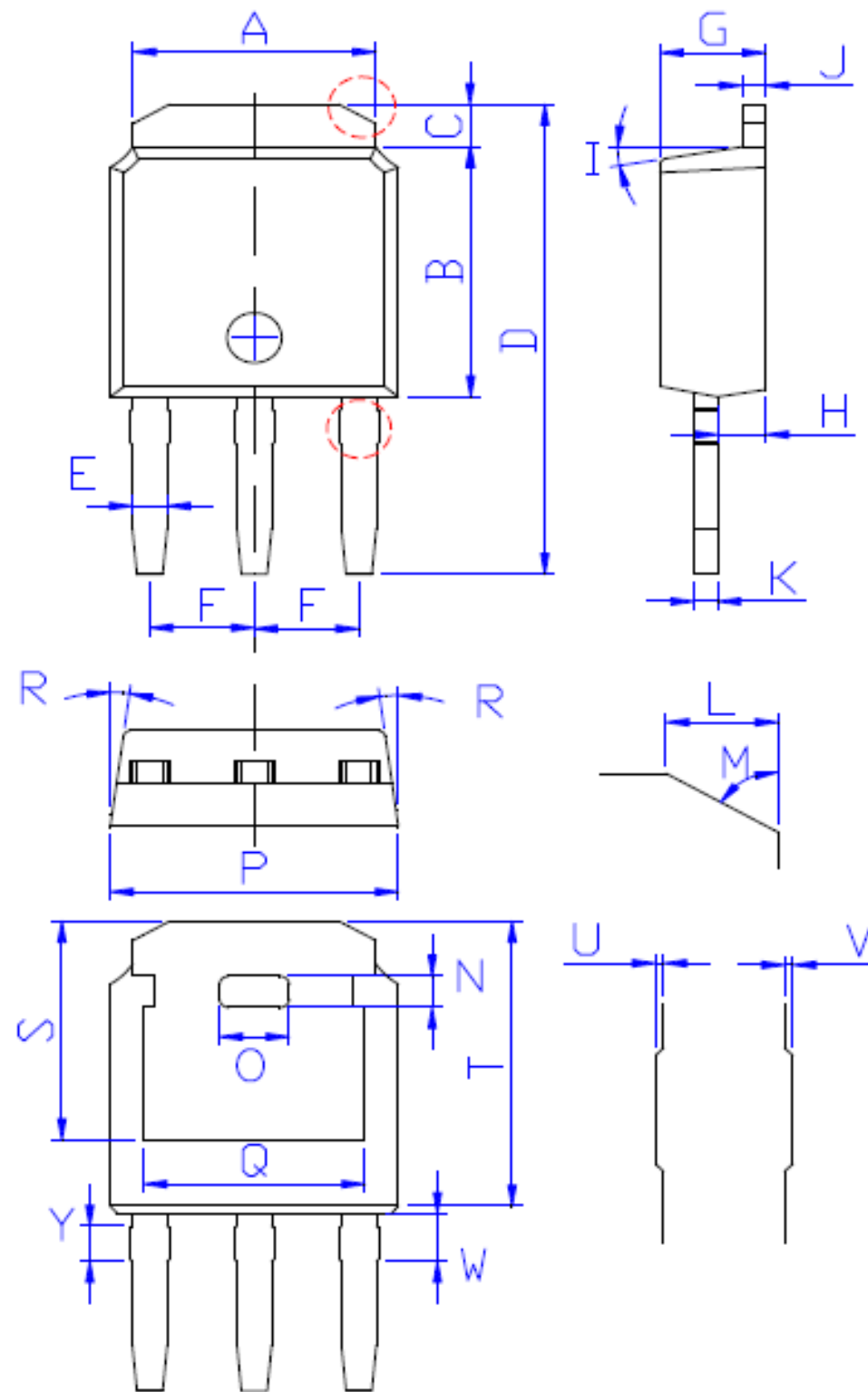


标注	尺寸(mm)
E	9.88±0.10
E1	7.40±0.20
E2	9.90±0.15
L	15.20±0.25
L1	1.30±0.15
L2	1.60±0.10
L3	13.00±0.20
L4	10.40±0.15
L5	2.60±0.15
L6	4.80±0.20
b	0.80±0.07
b1	1.27±0.07
b2	0.05±0.07
C	4.48±0.10
C1	1.30±0.07
C2	0.50±0.07
C3	2.40±0.06
C4	0.10±0.08
C5	0.10±0.08
D	9.20±0.10
D1	8.00±0.10
D2	8.00±0.10
R	0.50±0.10
θ1	15° ±2°
θ2	3° ±2°
θ3	3° ±2°
θ4	3° ±2°
θ5	3° ±2°
θ6	0° ~6°
θ7	13° ±2°
e	5.08±0.10
DIA	宽 1.50±0.10 深 0.30±0.15

外形尺寸:

Package Dimension:

TO-251



DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	11.31±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	0.75±0.30
O	1.80±0.30
P	6.60±0.30
Q	4.85±0.30
R	(4-8.5)°
S	5.30±0.30
T	6.90±0.30
U	0.05±0.05
V	0.05±0.05
W	1.15±0.25
Y	0.85±0.25

(Unit: mm)